

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yi-Fan Chen, Examiner: Huynh, Andy  
5 Chi-King Pu,  
Shou-Kong Fan

Filing Date: 04/18/01 Art Unit: 2818

Serial No.: 09/836,258 Docket No.: NAUP0280USA

8/B  
G. Staley  
7-16-02

10 Title: BYPASS CIRCUITS FOR REDUCING PLASMA DAMAGE

To: The Commissioner of Patents and Trademarks  
Washington, D.C. 20231

15 Subject: Response to the Office Action dated 05/03/2002

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Dear Sir:

JUL 11 2002

AMENDMENT

TECHNOLOGY CENTER 2800

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In response to the Office Action identified above,  
please amend the above-identified application as  
follows:

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In the claims:

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B1  
1. (Once amended) A bypass circuit for reducing plasma  
damage to a gate oxide of a metal-oxide semiconductor  
(MOS) wafer, the bypass circuit positioned on a  
semiconductor wafer, the semiconductor wafer  
comprising a substrate, the MOS transistor, a  
dielectric layer, and the bypass circuit, respectively,  
with the bypass circuit comprising: